

IRF530 Information



For Reference Only

Part Number IRF530

Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 100V 14A TO-220AB

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



Request a Quote

Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









IRF530 Specifications

Manufacturer Part Number IRF530 Manufacturer Vishay Siliconix Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 14A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 26nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 670pF @ 25V Vgs (Max) ± 20V FET Feature - Power Dissipation (Max) 88W (Tc) Rds On (Max) @ Id, Vgs 160 mOhm @ 8.4A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220AB		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 14A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 26nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 670pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 88W (Tc) Rds On (Max) @ Id, Vgs 160 mOhm @ 8.4A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220AB	Manufacturer Part Number	IRF530
Package TO-220-3 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 14A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 26nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 670pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 88W (Tc) Rds On (Max) @ Id, Vgs 160 mOhm @ 8.4A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Manufacturer	Vishay Siliconix
Package TO-220-3 Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 14A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250μA Gate Charge (Qg) (Max) @ Vgs 26nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 670pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 88W (Tc) Rds On (Max) @ Id, Vgs 160 mOhm @ 8.4A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Category	Discrete Semiconductor Products
Series - N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 14A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4V @ 250µA Gate Charge (Qg) (Max) @ Vgs 26nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 670pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 88W (Tc) Rds On (Max) @ Id, Vgs 160 mOhm @ 8.4A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case 100V		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C14A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs26nC @ 10VInput Capacitance (Ciss) (Max) @ Vds670pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)88W (Tc)Rds On (Max) @ Id, Vgs160 mOhm @ 8.4A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Package	TO-220-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C14A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs26nC @ 10VInput Capacitance (Ciss) (Max) @ Vds670pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)88W (Tc)Rds On (Max) @ Id, Vgs160 mOhm @ 8.4A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Series	-
Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C14A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs26nC @ 10VInput Capacitance (Ciss) (Max) @ Vds670pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)88W (Tc)Rds On (Max) @ Id, Vgs160 mOhm @ 8.4A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C14A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs26nC @ 10VInput Capacitance (Ciss) (Max) @ Vds670pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)88W (Tc)Rds On (Max) @ Id, Vgs160 mOhm @ 8.4A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs26nC @ 10VInput Capacitance (Ciss) (Max) @ Vds670pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)88W (Tc)Rds On (Max) @ Id, Vgs160 mOhm @ 8.4A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Drain to Source Voltage (Vdss)	100V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 670pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 160 mOhm @ 8.4A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-220AB	Current - Continuous Drain (Id) @ 25°C	14A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 670pF @ 25V Vgs (Max) ±20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 160 mOhm @ 8.4A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-220AB TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) E20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 160 mOhm @ 8.4A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)88W (Tc)Rds On (Max) @ Id, Vgs160 mOhm @ 8.4A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Gate Charge (Qg) (Max) @ Vgs	26nC @ 10V
FET Feature - Power Dissipation (Max) 88W (Tc) Rds On (Max) @ Id, Vgs 160 mOhm @ 8.4A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Input Capacitance (Ciss) (Max) @ Vds	670pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 160 mOhm @ 8.4A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs160 mOhm @ 8.4A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Power Dissipation (Max)	88W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	160 mOhm @ 8.4A, 10V
Supplier Device Package TO-220AB Package / Case TO-220-3	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220AB
Report errors?	Package / Case	TO-220-3
		Report errors?

IRF530 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRF530 Payment Methods





















IRF530 Shipping Methods













If you have any question about IRF530, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com